

12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20231219004.1

Qualification of RFAB as an additional Fab site option, die revision, and new Assembly site/BOM Options for select devices

Change Notification / Sample Request

Date: December 21, 2023 **To:** Newark/Farnell PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments (TI). The details of this change are on the following pages, and are in alignment with our standard product change notification (PCN) <u>process.</u>

TI requires acknowledgement of receipt of this notification within 30 days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 30 days of this notification, given that samples are not built ahead of the change.

The Proposed First Ship date in this PCN letter is the earliest possible date that customers could receive the changed material. It is our commitment that the changed device will not ship before that date. If samples are requested within the 30 day sample request window, customers will still have 30-days to complete their evaluation regardless of the proposed 1st ship date.

This particular PCN is related to TI's multiyear transition plan for our two remaining factories with 150-millimeter production (DFAB in Dallas, Texas, and SFAB in Sherman, Texas). DFAB will remain open, but will focus on 200-mm production, with a smaller set of technologies. SFAB will close no earlier than 2024 and no later than 2025. As referenced in the "reason for change" below, these changes are part of our multiyear plan to transition these products to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the Change Management team. For sample requests or sample related questions, contact your local Field Sales Representative. As always, we thank you for your continued business.

Change Management Team SC Business Services

20231219004.1 Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE TPS 5430 DDA

CUSTOMER PART NUMBER

null

Technical details of this Product Change follow on the next page(s).

PCN Number: 20			202	231219004.1				PCN Date: December 21, 2023				
Title:		Qualification of RFAB as an additional Fab site option, die revision, and new Asse									n, and new Assembly	
1100		site/BOI	M Optic	ions for select devices								
Custo	omer (Contact	:		Chang	je M	1anagement Te	eam	Dep	t:		Quality Services
Proposed 1st Ship Date: Ma				Mar 1	9, 2	2024		ple requests par			Jan 20, 2024*	
*Sam	*Sample requests received after Jan 20, 2024 will not be supported.											
Chan	ge Ty	pe:										
\boxtimes	Asser	mbly Site	9			\boxtimes	Design				Waf	fer Bump Material
	Asser	mbly Pro	cess				Data Sheet				Waf	fer Bump Process
X	Assembly Materials						Part number change			\boxtimes	Waf	fer Fab Site
■ Mechanical Specification						Test Site		₩a		Waf	fer Fab Material	
☐ Packing/Shipping/Labeling						Test Process			\boxtimes	Waf	fer Fab Process	
							PCN Detai	ls				

Description of Change:

Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab option and die revision in addition to BOM options for the devices listed below.

Cı	urrent Fab Site	•	Additional Fab site				
Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter		
DL-LIN	LBC4	150mm	RFAB	LBC9	200mm		
CFAB	LBC4	200mm	KFAD	LDC9	300mm		

The die was also changed as a result of the process change.

Construction differences are as follows (No constructions differences for Group 2 Devices:

Group 1 BOM Table (RFAB/Process migration, Die Change & Qualify ASESH as an additional Assembly site):

	AP1	ASESH
Mold Compound	SID#101379294	SID#EN2000784
Mount Compound	SID#101374994	SID#EY1000102

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change	⊠ No Change	⊠ No Change	⊠ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
CFAB	CU3	CHN	Chengu
RFAB	RFB	USA	Richardson

Die Rev:

Current New

	_
Die Rev [2P]	Die Rev [2P]
Α	A

Assembly Site Information:

ASESH	ASH	CHN	Shanghai	
AP1	AKR	PHL	Cupang, Muntinlupa City	
Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City	

Sample product shipping label (not actual product label):



ያየጀሕ: LBL: 5A (L)T0:39750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483812

(2P) REV: (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

Group 1 Device list (RFAB/Process migration, Die Change & Qualify ASESH as an additional Assembly site):

TPS5430DDA TPS5430DDAR TPS5431DDA TPS5431DDAR

Group 2 Device list (RFAB/Process migration, Die change only):

TPS5410D TPS5410DR TPS5420D TPS5420DR

For alternate parts with similar or improved performance, please visit the product page on TI.com

Qualification Report

Approve Date 30-August-2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: LMR54450DDARR	Wafer fab QBS Reference: <u>LMR33620CQRNXTQ1</u>	Package QBS Reference: LMR38010FDDAR
HAST	A2	Temperature Humidity Bias	85C/85%RH	1000 Hours	QBS		-3/231/0
UHAST	А3	Unbiased HAST	130C/85%RH	96 Hours	3/231/0	-	-
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	3/231/0		-
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	QBS		3/231/0
HTOL	B1	Life Test	125C	1000 Hours	1/77/0	3/231/0	
ESD	E2	ESD CDM	-	750 Volts	1/3/0		-
ESD	E2	ESD HBM	-	2500 Volts	1/3/0		-
LU	E4	Latch-Up	Per JESD78	-	1/6/0		-

- QBS: Qual By Similarity
- Qual Device LMR54450DDAR is qualified at MSL1 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2203-106

Change Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Qualification for TPS542xQDRQ1 family in RFAB Approve Date 10-August-2023

Product Attributes

Attributes	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:
Auributes	TPS5420QDRQ1	LMR33620CQRNXTQ1	SN65HVDA1040AQDRQ1	TLV9064QDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Interface	
Wafer Fab Supplier	RFAB	RFAB	DL-LIN	RFAB
Assembly Site	MLA	UTL1	MLA	MLA
Package Group	SOIC			SOIC
Package Designator	D	RNX	D	D
Pin Count	8	12	8	14

- QBS: Qual By Similarity
 Qual Device TPS5420QDRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Type # Test Spec		Min SS / Test Spec Lot Lot Qty		Test Name	Condition	Duration	Qual Device: TPS5420QDRQ1	QBS Reference: LMR33620CQRNXTQ1	QBS Reference: Package #1	QBS Reference: package #2
			Qty							SN65HVDA1040AQDRQ1	TLV9064QDRQ1
Test Group	A - Acce	elerated Enviror	ment St	ress Tes	sts						
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	-	1/154/0		3/693/0	
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C		-		-	3/693/0 plus 1/45/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C	96 Hours	-			-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0		3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours			3/231/0	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65/150C	500 Cycles	1/77/0		3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0		-	-
PTC	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles			-	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-			3/231/0
Test Group	B - Acce	elerated Lifetime	e Simula	tion Tes	ts						
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	1/77/0	3/231/0		
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	3/2400/0		

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS5420QDRQ1	QBS Reference: LMR33620CQRNXTQ1	QBS Reference: Package #1 SN65HVDA1040AQDRQ1	QBS Reference: package #2 TLV9064QDRQ1
Test Group	C - Pack	age Assembly	Integrity	Tests							
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-		
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0			
SD	C3	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-		
SD	C3	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-		
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0		3/30/0	
Test Group	D - Die F	abrication Relia	ability Te	sts							
ЕМ	D1	JESD61		-	Electromigration	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35			Time Dependent Dielectric Breakdown	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-		-	Negative Bias Temperature Instability	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS5420QDRQ1	QBS Reference: LMR33620CQRNXTQ1	QBS Reference: Package #1 SN65HVDA1040AQDRQ1	QBS Reference: package #2 <u>TLV9064QDRQ1</u>
Test Group	E - Elect	rical Verification	n Tests								
ESD	E2	AEC Q100- 002	1	3	ESD HBM		2000 Volts	1/3/0			
ESD	E3	AEC Q100- 011	1	3	ESD CDM		500 Volts	1/3/0			
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0			

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

3/30/0

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

Cpk>1.67 Room, hot, and cold

- $\bullet \quad \text{The following are equivalent HTSL options based on an activation energy of 0.7eV: } 150\text{C/1k Hours, and } 170\text{C/420 Hours}$
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Electrical

Distributions

Ambient Operating Temperature by Automotive Grade Level:

AEC Q100-009

3

30

Grade 0 (or E): -40C to +150C

E5

ED

Additional Tests

- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2203-107

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.